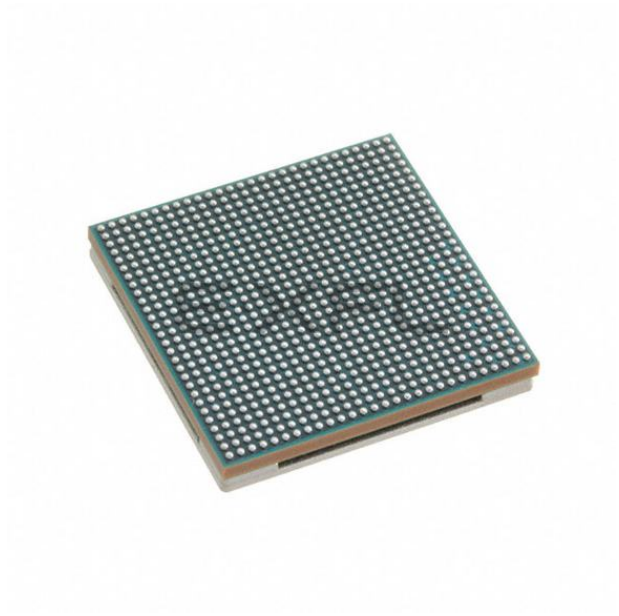


Welcome to E-XFL.COM

Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	481000
Total RAM Bits	33792000
Number of I/O	388
Number of Gates	-
Voltage - Supply	0.97V ~ 1.08V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 100°C (TJ)
Package / Case	784-BBGA, FCBGA
Supplier Device Package	784-FCBGA (29x29)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/mpf500t-1fcg784e

4 Device Offering

The following table lists the PolarFire FPGA device options using the MPF300T as an example. The MPF100T, MPF200T, and MPF500T device densities have identical offerings.

Table 1 • PolarFire FPGA Device Options

Device Options	Extended Commercial 0 °C–100 °C	Industrial –40 °C–100 °C	STD	–1	Transceivers T	Lower Static Power L	Data Security S
MPF300T	Yes	Yes	Yes	Yes	Yes		
MPF300TL	Yes	Yes	Yes		Yes	Yes	
MPF300TS		Yes	Yes	Yes	Yes		Yes
MPF300TLS		Yes	Yes		Yes	Yes	Yes

I/O Standard	V_{DDI} Min (V)	V_{DDI} Typ (V)	V_{DDI} Max (V)	V_{OL} Min (V)	V_{OL} Max (V)	V_{OH} Min (V)	V_{OH} Max (V)	I_{OL}[2,6] mA	I_{OH}[2,6] mA
HSTL135I[4]	1.283	1.35	1.418		0.2 × V_{DDI}	0.8 × V_{DDI}		V_{OL}/50	(V_{DDI} – V_{OH}) /50
HSTL135II[4]	1.283	1.35	1.418		0.2 × V_{DDI}	0.8 × V_{DDI}		V_{OL}/25	(V_{DDI} – V_{OH}) /25
HSTL12I[4]	1.14	1.2	1.26		0.1 × V_{DDI}	0.9 × V_{DDI}		V_{OL}/50	(V_{DDI} – V_{OH}) /50
HSTL12II[4]	1.14	1.2	1.26		0.1 × V_{DDI}	0.9 × V_{DDI}		V_{OL}/25	(V_{DDI} – V_{OH}) /25
HSUL18I[4]	1.71	1.8	1.89		0.1 × V_{DDI}	0.9 × V_{DDI}		V_{OL}/55	(V_{DDI} – V_{OH}) /55
HSUL18II[4]	1.71	1.8	1.89		0.1 × V_{DDI}	0.9 × V_{DDI}		V_{OL}/25	(V_{DDI} – V_{OH}) /25
HSUL12I[4]	1.14	1.2	1.26		0.1 × V_{DDI}	0.9 × V_{DDI}		V_{OL}/40	(V_{DDI} – V_{OH}) /40
POD12I[4,5]	1.14	1.2	1.26		0.5 × V_{DDI}			V_{OL}/48	(V_{DDI} – V_{OH}) /48
POD12II[4,5]	1.14	1.2	1.26		0.5 × V_{DDI}			V_{OL}/34	(V_{DDI} – V_{OH}) /34

1. Drive strengths per PCI specification V/I curves.
2. Refer to UG0686: PolarFire FPGA User I/O User Guide for details on supported drive strengths.
3. For external stub-series resistance. This resistance is on-die for GPIO.
4. I_{OL}/I_{OH} units for impedance standards in amps (not mA).
5. VOH_MAX based on external pull-up termination (pseudo-open drain).
6. The total DC sink/source current of all IOs within a lane is limited as follows:
   a. HSIO lane: 120 mA per 12 IO buffers.
   b. GPIO lane: 160 mA per 12 IO buffers.

Note: 3.3 V and 2.5 V are only supported in GPIO banks.

6.3.2 Differential DC Input and Output Levels

The follow tables list the differential DC I/O levels.

Table 14 • Differential DC Input Levels

I/O Standard	Bank Type	VICM_RANGE Libero Setting	V_{ICM}[1,3] Min (V)	V_{ICM}[1,3] Typ (V)	V_{ICM}[1,3] Max (V)	V_{ID}[2] Min (V)	V_{ID} Typ (V)	V_{ID} Max (V)
LVDS33	GPIO	Mid (default)	0.6	1.25	2.35	0.1	0.35	0.6
		Low	0.05	0.4	0.8	0.1	0.35	0.6
LVDS25	GPIO	Mid (default)	0.6	1.25	2.35	0.1	0.35	0.6
		Low	0.05	0.4	0.8	0.1	0.35	0.6
LVDS18[4]	GPIO	Mid (default)	0.6	1.25	1.65	0.1	0.35	0.6

Min (%)	Typ	Max (%)	Unit	Condition
–20	60	20	Ω	V_{DDI} = 1.2 V
–20	120	20	Ω	V_{DDI} = 1.2 V

Note: Thevenin impedance is calculated based on independent P and N as measured at 50% of V_{DDI}. For 50 Ω/75 Ω/150 Ω cases, nearest supported values of 40 Ω/60 Ω/120 Ω are used.

Table 19 • Single-Ended Termination to VDDI (Internal Parallel Termination to VDDI)

Min (%)	Typ	Max (%)	Unit	Condition
–20	34	20	Ω	V_{DDI} = 1.2 V
–20	40	20	Ω	V_{DDI} = 1.2 V
–20	48	20	Ω	V_{DDI} = 1.2 V
–20	60	20	Ω	V_{DDI} = 1.2 V
–20	80	20	Ω	V_{DDI} = 1.2 V
–20	120	20	Ω	V_{DDI} = 1.2 V
–20	240	20	Ω	V_{DDI} = 1.2 V

Note: Measured at 80% of V_{DDI}.

Table 20 • Single-Ended Termination to VSS (Internal Parallel Termination to VSS)

Min (%)	Typ	Max (%)	Unit	Condition
–20	120	20	Ω	V_{DDI} = 1.8 V/1.5 V
–20	240	20	Ω	V_{DDI} = 1.8 V/1.5 V
–20	120	20	Ω	V_{DDI} = 1.2 V
–20	240	20	Ω	V_{DDI} = 1.2 V

Note: Measured at 50% of V_{DDI}.

6.3.5 GPIO On-Die Termination

The following table lists the on-die termination calibration accuracy specifications for GPIO bank.

Table 21 • On-Die Termination Calibration Accuracy Specifications for GPIO Bank

Parameter	Description	Min (%)	Typ	Max (%)	Unit	Condition
Differential termination[1]	Internal differential termination	–20	100	20	Ω	V_{ICM} < 0.8 V
		–20	100	40	Ω	0.6 V < V_{ICM} < 1.65 V
		–20	100	80	Ω	1.4 V < V_{ICM}
Single-ended thevenin termination[2, 3]	Internal parallel thevenin termination	–40	50	20	Ω	V_{DDI} = 1.8 V/1.5 V
		–40	75	20	Ω	V_{DDI} = 1.8 V
		–40	150	20	Ω	V_{DDI} = 1.8 V
		–20	20	20	Ω	V_{DDI} = 1.5 V
		–20	30	20	Ω	V_{DDI} = 1.5 V
		–20	40	20	Ω	V_{DDI} = 1.5 V
		–20	60	20	Ω	V_{DDI} = 1.5 V
		–20	120	20	Ω	V_{DDI} = 1.5 V

Standard	Description	V_L[1]	V_H[1]	V_{ID}[2]	V_{ICM}[2]	V_{MEAS}[3, 4]	V_{REF}[1, 5]	Unit
HSUL18I	HSUL 1.8 V Class I	V_{REF} – 0.54	V_{REF} + 0.54			V_{REF}	0.90	V
HSUL18II	HSUL 1.8 V Class II	V_{REF} – 0.54	V_{REF} + 0.54			V_{REF}	0.90	V
HSUL12	HSUL 1.2 V	V_{REF} – .22	V_{REF} + .22			V_{REF}	0.60	V
POD12I	Pseudo open drain (POD) logic 1.2 V Class I	V_{REF} – .15	V_{REF} + .15			V_{REF}	0.84	V
POD12II	POD 1.2 V Class II	V_{REF} – .15	V_{REF} + .15			V_{REF}	0.84	V
LVDS33	Low-voltage differential signaling (LVDS) 3.3 V	V_{ICM} – .125	V_{ICM} + .125	0.250	1.250	0		V
LVDS25	LVDS 2.5 V	V_{ICM} – .125	V_{ICM} + .125	0.250	1.250	0		V
LVDS18	LVDS 1.8 V	V_{ICM} – .125	V_{ICM} + .125	0.250	0.900	0		V
RSDS33	RSDS 3.3 V	V_{ICM} – .125	V_{ICM} + .125	0.250	1.250	0		V
RSDS25	RSDS 2.5 V	V_{ICM} – .125	V_{ICM} + .125	0.250	1.250	0		V
RSDS18	RSDS 1.8 V	V_{ICM} – .125	V_{ICM} + .125	0.250	1.250	0		V
MINILVDS33	Mini-LVDS 3.3 V	V_{ICM} – .125	V_{ICM} + .125	0.250	1.250	0		V
MINILVDS25	Mini-LVDS 2.5 V	V_{ICM} – .125	V_{ICM} + .125	0.250	1.250	0		V
MINILVDS18	Mini-LVDS 1.8 V	V_{ICM} – .125	V_{ICM} + .125	0.250	1.250	0		V
SUBLVDS33	Sub-LVDS 3.3 V	V_{ICM} – .125	V_{ICM} + .125	0.250	0.900	0		V
SUBLVDS25	Sub-LVDS 2.5 V	V_{ICM} – .125	V_{ICM} + .125	0.250	0.900	0		V
SUBLVDS18	Sub-LVDS 1.8 V	V_{ICM} – .125	V_{ICM} + .125	0.250	0.900	0		V
PPDS33	Point-to-point differential signaling 3.3 V	V_{ICM} – .125	V_{ICM} + .125	0.250	0.800	0		V
PPDS25	PPDS 2.5 V	V_{ICM} – .125	V_{ICM} + .125	0.250	0.800	0		V
PPDS18	PPDS 1.8 V	V_{ICM} – .125	V_{ICM} + .125	0.250	0.800	0		V
SLVS33	Scalable low-voltage signaling 3.3 V	V_{ICM} – .125	V_{ICM} + .125	0.250	0.200	0		V

Standard	Description	V_L[1]	V_H[1]	V_{ID}[2]	V_{ICM}[2]	V_{MEAS}[3, 4]	V_{REF}[1, 5]	Unit
SLVS25	SLVS 2.5 V	V_{ICM} – .125	V_{ICM} + .125	0.250	0.200	0		V
SLVS18	SLVS 1.8 V	V_{ICM} – .125	V_{ICM} + .125	0.250	0.200	0		V
HCSL33	High-speed current steering logic (HCSL) 3.3 V	V_{ICM} – .125	V_{ICM} + .125	0.250	0.350	0		V
HCSL25	HCSL 2.5 V	V_{ICM} – .125	V_{ICM} + .125	0.250	0.350	0		V
HCSL18	HCSL 1.8 V	V_{ICM} – .125	V_{ICM} + .125	0.250	0.350	0		V
BLVDSE25[6]	Bus LVDS 2.5 V	V_{ICM} – .125	V_{ICM} + .125	0.250	1.250	0		V
MLVDSE25[6]	Multipoint LVDS 2.5 V	V_{ICM} – .125	V_{ICM} + .125	0.250	1.250	0		V
LVPECL33	Low-voltage positive emitter coupled logic	V_{ICM} – .125	V_{ICM} + .125	0.250	1.650	0		V
LVPECLE33[6]	Low-voltage positive emitter coupled logic	V_{ICM} – .125	V_{ICM} + .125	0.250	1.650	0		V
SSTL25I	Differential SSTL 2.5 V Class I	V_{ICM} – .125	V_{ICM} + .125	0.250	1.250	0		V
SSTL25II	Differential SSTL 2.5 V Class II	V_{ICM} – .125	V_{ICM} + .125	0.250	1.250	0		V
SSTL18I	Differential SSTL 1.8 V Class I	V_{ICM} – .125	V_{ICM} + .125	0.250	0.900	0		V
SSTL18II	Differential SSTL 1.8 V Class II	V_{ICM} – .125	V_{ICM} + .125	0.250	0.900	0		V
SSTL15	Differential SSTL 1.5 V Class I	V_{ICM} – .125	V_{ICM} + .125	0.250	0.750	0		V
SSTL135	Differential SSTL 1.5 V Class II	V_{ICM} – .125	V_{ICM} + .125	0.250	0.750	0		V
HSTL15I	Differential HSTL 1.5 V Class I	V_{ICM} – .125	V_{ICM} + .125	0.250	0.750	0		V
HSTL15II	Differential HSTL 1.5 V Class II	V_{ICM} – .125	V_{ICM} + .125	0.250	0.750	0		V
HSTL135I	Differential HSTL 1.35 V Class I	V_{ICM} – .125	V_{ICM} + .125	0.250	0.675	0		V

Standard	Description	V_L[1]	V_H[1]	V_{ID}[2]	V_{ICM}[2]	V_{MEAS}[3,4]	V_{REF}[1,5]	Unit
HSTL135II	Differential HSTL 1.35 V Class II	V_{ICM} – .125	V_{ICM} + .125	0.250	0.675	0		V
HSTL12	Differential HSTL 1.2 V	V_{ICM} – .125	V_{ICM} + .125	0.250	0.600	0		V
HSUL18I	Differential HSUL 1.8 V Class I	V_{ICM} – .125	V_{ICM} + .125	0.250	0.900	0		V
HSUL18II	Differential HSUL 1.8 V Class II	V_{ICM} – .125	V_{ICM} + .125	0.250	0.900	0		V
HSUL12	Differential HSUL 1.2 V	V_{ICM} – .125	V_{ICM} + .125	0.250	0.600	0		V
POD12I	Differential POD 1.2 V Class I	V_{ICM} – .125	V_{ICM} + .125	0.250	0.600	0		V
POD12II	Differential POD 1.2 V Class II	V_{ICM} – .125	V_{ICM} + .125	0.250	0.600	0		V
MIPI25	Mobile Industry Processor Interface	V_{ICM} – .125	V_{ICM} + .125	0.250	0.200	0		V

1. Measurements are made at typical, minimum, and maximum V_{REF} values. Reported delays reflect worst-case of these measurements. V_{REF} values listed are typical. Input waveform switches between V_L and V_H. All rise and fall times must be 1 V/ns.
2. Differential receiver standards all use 250 mV V_{ID} for timing. V_{CM} is different between different standards.
3. Input voltage level from which measurement starts.
4. The value given is the differential input voltage.
5. This is an input voltage reference that bears no relation to the V_{REF}/V_{MEAS} parameters found in IBIS models or shown in Output Delay Measurement—Single-Ended Test Setup (see page 27).
6. Emulated bi-directional interface.

7.1.2 Output Delay Measurement Methodology

The following section provides information about the methodology for output delay measurement.

Table 23 • Output Delay Measurement Methodology

Standard	Description	R_{REF} (Ω)	C_{REF} (pF)	V_{MEAS} (V)	V_{REF} (V)
PCI	PCIE 3.3 V	25	10	1.65	
LVTTL33	LVTTL 3.3 V	1M	0	1.65	
LVCMOS33	LVCMOS 3.3 V	1M	0	1.65	
LVCMOS25	LVCMOS 2.5 V	1M	0	1.25	
LVCMOS18	LVCMOS 1.8 V	1M	0	0.90	
LVCMOS15	LVCMOS 1.5 V	1M	0	0.75	
LVCMOS12	LVCMOS 1.2 V	1M	0	0.60	
SSTL25I	Stub-series terminated logic 2.5 V Class I	50	0	V_{REF}	1.25
SSTL25II	SSTL 2.5 V Class II	50	0	V_{REF}	1.25

Figure 1 • Output Delay Measurement—Single-Ended Test Setup

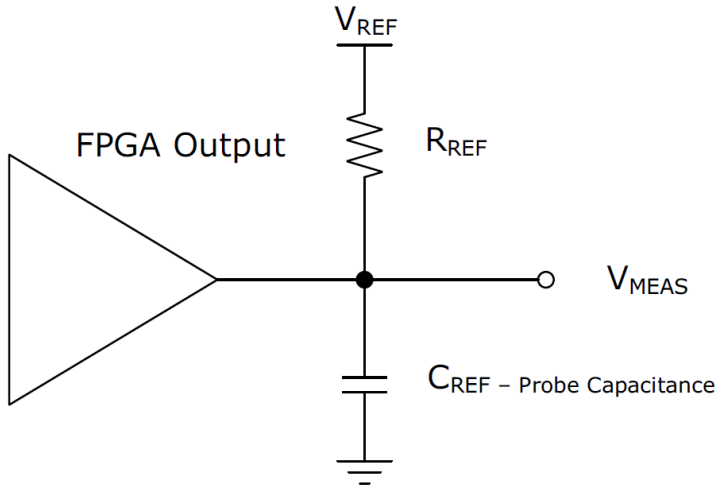
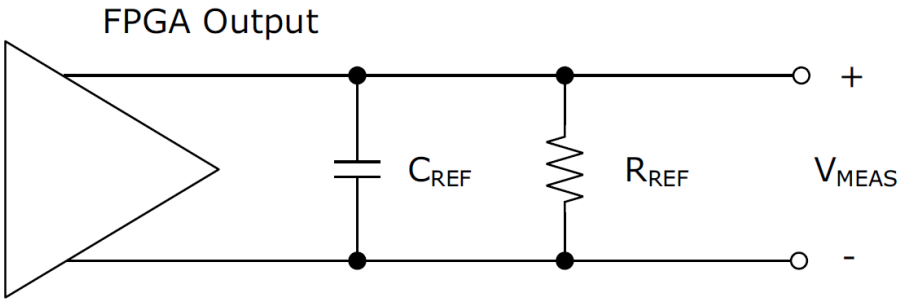


Figure 2 • Output Delay Measurement—Differential Test Setup



7.1.3 Input Buffer Speed

The following tables provide information about input buffer speed.

Table 24 • HSIO Maximum Input Buffer Speed

Standard	STD	–1	Unit
LVDS18	1250	1250	Mbps
RSDS18	800	800	Mbps
MINILVDS18	800	800	Mbps
SUBLVDS18	800	800	Mbps
PPDS18	800	800	Mbps
SLVS18	800	800	Mbps
SSTL18I	800	1066	Mbps
SSTL18II	800	1066	Mbps
SSTL15I	1066	1333	Mbps
SSTL15II	1066	1333	Mbps
SSTL135I	1066	1333	Mbps
SSTL135II	1066	1333	Mbps

Standard	STD	–1	Unit
LVCMOS18 (12 mA)	500	500	Mbps
LVCMOS15 (10 mA)	500	500	Mbps
LVCMOS12 (8 mA)	300	300	Mbps
MIPI25/MIPI33	800	800	Mbps

1. All SSTLD/HSTLD/HSULD/LVSTLD/POD type receivers use the LVDS differential receiver.
2. Performance is achieved with V_{ID} ≥200 mV.

7.1.4 Output Buffer Speed

Table 26 • HSIO Maximum Output Buffer Speed

Standard	STD	–1	Unit
SSTL18I	800	1066	Mbps
SSTL18II	800	1066	Mbps
SSTL18I (differential)	800	1066	Mbps
SSTL18II (differential)	800	1066	Mbps
SSTL15I	1066	1333	Mbps
SSTL15II	1066	1333	Mbps
SSTL15I (differential)	1066	1333	Mbps
SSTL15II (differential)	1066	1333	Mbps
SSTL135I	1066	1333	Mbps
SSTL135II	1066	1333	Mbps
SSTL135I (differential)	1066	1333	Mbps
SSTL135II (differential)	1066	1333	Mbps
HSTL15I	900	1100	Mbps
HSTL15II	900	1100	Mbps
HSTL15I (differential)	900	1100	Mbps
HSTL15II (differential)	900	1100	Mbps
HSTL135I	1066	1066	Mbps
HSTL135II	1066	1066	Mbps
HSTL135I (differential)	1066	1066	Mbps
HSTL135II (differential)	1066	1066	Mbps
HSUL18I	400	400	Mbps
HSUL18II	400	400	Mbps
HSUL18II (differential)	400	400	Mbps
HSUL12	1066	1333	Mbps
HSUL12I (differential)	1066	1333	Mbps
HSTL12	1066	1266	Mbps
HSTL12I (differential)	1066	1266	Mbps
POD12I	1333	1600	Mbps
POD12II	1333	1600	Mbps
LVCMOS18 (12 mA)	500	500	Mbps
LVCMOS15 (10 mA)	500	500	Mbps

Standard	STD	–1	Unit
LVCMOS12 (8 mA)	250	300	Mbps

Table 27 • GPIO Maximum Output Buffer Speed

Standard	STD	–1	Unit
LVDS25/LCMDS25	1250	1250	Mbps
LVDS33/LCMDS33	1250	1600	Mbps
RSDS25	800	800	Mbps
MINILVDS25	800	800	Mbps
SUBLVDS25	800	800	Mbps
PPDS25	800	800	Mbps
SLVSE15	500	500	Mbps
BUSLVDSE25	500	500	Mbps
MLVDSE25	500	500	Mbps
LVPECLE33	500	500	Mbps
SSTL25I	800	800	Mbps
SSTL25II	800	800	Mbps
SSTL25I (differential)	800	800	Mbps
SSTL25II (differential)	800	800	Mbps
SSTL18I	800	800	Mbps
SSTL18II	800	800	Mbps
SSTL18I (differential)	800	800	Mbps
SSTL18II (differential)	800	800	Mbps
SSTL15I	800	1066	Mbps
SSTL15II	800	1066	Mbps
SSTL15I (differential)	800	1066	Mbps
SSTL15II (differential)	800	1066	Mbps
HSTL15I	900	900	Mbps
HSTL15II	900	900	Mbps
HSTL15I (differential)	900	900	Mbps
HSTL15II (differential)	900	900	Mbps
HSUL18I	400	400	Mbps
HSUL18II	400	400	Mbps
HSUL18I (differential)	400	400	Mbps
HSUL18II (differential)	400	400	Mbps
PCI	500	500	Mbps
LVTTL33 (20 mA)	500	500	Mbps
LVCMOS33 (20 mA)	500	500	Mbps
LVCMOS25 (16 mA)	500	500	Mbps
LVCMOS18 (12 mA)	500	500	Mbps
LVCMOS15 (10 mA)	500	500	Mbps
LVCMOS12 (8 mA)	250	300	Mbps
MIPIE25	500	500	Mbps

7.1.5 Maximum PHY Rate for Memory Interface IP

The following tables provide information about the maximum PHY rate for memory interface IP.

Table 28 • Maximum PHY Rate for Memory Interfaces IP for HSIO Banks

Memory Standard	Gearing Ratio	V_{DDAUX}	V_{DDI}	STD (Mbps)	–1 (Mbps)	Fabric STD (MHz)	Fabric –1 (MHz)
DDR4	8:1	1.8 V	1.2 V	1333	1600	167	200
DDR3	8:1	1.8 V	1.5 V	1067	1333	133	167
DDR3L	8:1	1.8 V	1.35 V	1067	1333	133	167
LPDDR3	8:1	1.8 V	1.2 V	1067	1333	133	167
QDRII+	8:1	1.8 V	1.5 V	900	1100	112.5	137.5
RLDRAM3[1]	8:1	1.8 V	1.35 V	1067	1067	133	133
RLDRAM3[1]	4:1	1.8 V	1.35 V	667	800	167	200
RLDRAM3[1]	2:1	1.8 V	1.35 V	333	400	167	200
RLDRAM2[1]	8:1	1.8 V	1.8 V	800	1067	100	133
RLDRAM2[1]	4:1	1.8 V	1.8 V	667	800	167	200
RLDRAM2[1]	2:1	1.8 V	1.8 V	333	400	167	200

1. RLDRAM2 and RLDRAM3 are not supported with a soft IP controller currently.

Table 29 • Maximum PHY Rate for Memory Interfaces IP for GPIO Banks

Memory Standard	Gearing Ratio	V_{DDAUX}	V_{DDI}	STD (Mbps)	–1 (Mbps)	Fabric STD (MHz)	Fabric –1 (MHz)
DDR3	8:1	2.5 V	1.5 V	800	1067	100	133
QDRII+	8:1	2.5 V	1.5 V	900	900	113	113
RLDRAM2[1]	4:1	2.5 V	1.8 V	800	800	200	200
RLDRAM2[1]	2:1	2.5 V	1.8 V	400	400	200	200

1. RLDRAM2 is currently not supported with a soft IP controller.

7.3 Fabric Specifications

The following section describes specifications for the fabric.

7.3.1 Math Blocks

The following tables describe math block performance.

Table 41 • Math Block Performance Extended Commercial Range (0 °C to 100 °C)

Parameter	Symbol	Modes	V_{DD} = 1.0 V – STD	V_{DD} = 1.0 V – 1	V_{DD} = 1.05 V – STD	V_{DD} = 1.05 V – 1	Unit
Maximum operating frequency	F_{MAX}	18 × 18 multiplication	370	470	440	500	MHz
		18 × 18 multiplication summed with 48-bit input	370	470	440	500	MHz
		18 × 19 multiplier pre-adder ROM mode	365	465	435	500	MHz
		Two 9 × 9 multiplication	370	470	440	500	MHz
		9 × 9 dot product (DOTP)	370	470	440	500	MHz
		Complex 18 × 19 multiplication	360	455	430	500	MHz

Table 42 • Math Block Performance Industrial Range (–40 °C to 100 °C)

Parameter	Symbol	Modes	V_{DD} = 1.0 V – STD	V_{DD} = 1.0 V – 1	V_{DD} = 1.05 V – STD	V_{DD} = 1.05 V – 1	Unit
Maximum operating frequency	F_{MAX}	18 × 18 multiplication	365	465	435	500	MHz
		18 × 18 multiplication summed with 48-bit input	365	465	435	500	MHz
		18 × 19 multiplier pre-adder ROM mode	355	460	430	500	MHz
		Two 9 × 9 multiplication	365	465	435	500	MHz
		9 × 9 DOTP	365	465	435	500	MHz
		Complex 18 × 19 multiplication	350	450	425	500	MHz

Table 44 • µSRAM Performance

Parameter	Symbol	V_{DD} = 1.0 V – STD	V_{DD} = 1.0 V – 1	V_{DD} = 1.05 V – STD	V_{DD} = 1.05 V – 1	Unit	Condition
Operating frequency	F_{MAX}	400	415	450	480	MHz	Write-port
Read access time	Tac		2		2	ns	Read-port

Table 45 • µPROM Performance

Parameter	Symbol	V_{DD} = 1.0 V – STD	V_{DD} = 1.0 V – 1	V_{DD} = 1.05 V – STD	V_{DD} = 1.05 V – 1	Unit
Read access time	Tac	10	10	10	10	ns

7.4 Transceiver Switching Characteristics

This section describes transceiver switching characteristics.

7.4.1 Transceiver Performance

The following table describes transceiver performance.

Table 46 • PolarFire Transceiver and TXPLL Performance

Parameter	Symbol	STD Min	STD Typ	STD Max	–1 Min	–1 Typ	–1 Max	Unit
Tx data rate[1,2]	F_{TXRate}	0.25		10.3125	0.25		12.7	Gbps
Tx OOB (serializer bypass) data rate	$F_{TXRateOOB}$	DC		1.5	DC		1.5	Gbps
Rx data rate when AC coupled[2]	$F_{RxRateAC}$	0.25		10.3125	0.25		12.7	Gbps
Rx data rate when DC coupled	$F_{RxRateDC}$	0.25		3.2	0.25		3.2	Gbps
Rx OOB (deserializer bypass) data rate	$F_{TXRateOOB}$	DC		1.25	DC		1.25	Gbps
TXPLL output frequency[3]	F_{TXPLL}	1.6		6.35	1.6		6.35	GHz
Rx CDR mode	F_{RXCDR}	0.25		10.3125	0.25		10.3125	Gbps
Rx DFE mode[2]	F_{RXDFE}	3.0		10.3125	3.0		12.7	Gbps
Rx Eye Monitor mode[2]	$F_{RXEyeMon}$	3.0		10.3125	3.0		12.7	Gbps

1. The reference clock is required to be a minimum of 75 MHz for data rates of 10 Gbps and above.
2. For data rates greater than 10.3125 Gbps, VDDA must be set to 1.05 V mode. See supply tolerance in the section Recommended Operating Conditions (see page 6).
3. The Tx PLL rate is between 0.5x to 5.5x the Tx data rate. The Tx data rate depends on per XCVR lane Tx post-divider settings.

7.4.2 Transceiver Reference Clock Performance

The following table describes performance of the transceiver reference clock.

Table 47 • PolarFire Transceiver Reference Clock AC Requirements

Parameter	Symbol	STD Min	STD Typ	STD Max	–1 Min	–1 Typ	–1 Max	Unit
Reference clock input rate[1, 2]	$F_{TXREFCLK}$	20		800	20		800	MHz

Parameter	Symbol	STD Min	STD Typ	STD Max	–1 Min	–1 Typ	–1 Max	Unit
Reference clock input rate[1, 2, 3]	$F_{XCVRREFCLKMAX\ CASCADE}$	20		156	20		156	MHz
Reference clock rate at the PFD[4]	$F_{TXREFCLKPFD}$	20		156	20		156	MHz
Reference clock rate recommended at the PFD for Tx rates 10 Gbps and above[4]	$F_{TXREFCLKPFD10G}$	75		156	75		156	MHz
Tx reference clock phase noise requirements to meet jitter specifications (156 MHz clock at reference clock input)[5]	$F_{TXREFPN}$			–110			–110	dBc /Hz
Phase noise at 10 KHz	$F_{TXREFPN}$			–110			–110	dBc /Hz
Phase noise at 100 KHz	$F_{TXREFPN}$			–115			–115	dBc /Hz
Phase noise at 1 MHz	$F_{TXREFPN}$			–135			–135	dBc /Hz
Reference clock input rise time (10%–90%)	$T_{REFRISE}$		200	500		200	500	ps
Reference clock input fall time (90%–10%)	$T_{REFFALL}$		200	500		200	500	ps
Reference clock duty cycle	$T_{REFDUTY}$	40		60	40		60	%
Spread spectrum modulation spread[6]	Mod_Spread	0.1		3.1	0.1		3.1	%
Spread spectrum modulation frequency[7]	Mod_Freq	TxREF CLKPFD/ (128)	32	TxREF CLKPFD/ (128*63)	TxREF CLKPFD/ (128)	32	TxREF CLKPFD/ (128*63)	KHz

1. See the maximum reference clock rate allowed per input buffer standard.
2. The minimum value applies to this clock when used as an XCVR reference clock. It does not apply when used as a non-XCVR input buffer (DC input allowed).
3. Cascaded reference clock.
4. After reference clock input divider.
5. Required maximum phase noise is scaled based on actual $F_{TxRefClkPFD}$ value by 20 × log10 (TxRefClkPFD /156 MHz). It is assumed that the reference clock divider of 4 is used for these calculations to always meet the maximum PFD frequency specification.
6. Programmable capability for depth of down-spread or center-spread modulation.
7. Programmable modulation rate based on the modulation divider setting (1 to 63).

7.4.3 Transceiver Reference Clock I/O Standards

The following table describes the differential I/O standards supported as transceiver reference clocks.

5. Improved jitter characteristics for a specific industry standard are possible in many cases due to improved reference clock or higher V_{CO} rate used.
6. Tx jitter is specified with all transmitters on the device enabled, a 10–12-bit error rate (BER) and Tx data pattern of PRBS7.
7. From the PMA mode, the TX_ELEC_IDLE port to the XVCR TXP/N pins.
   FTxRefClk = 75 MHz with typical settings.
   For data rates greater than 10.3125 Gbps, VDDA must be set to 1.05 V mode. See supply tolerance in the section Recommended Operating Conditions (see page 6). (see page 6)

7.4.6 Receiver Performance

The following table describes performance of the receiver.

Table 53 • PolarFire Transceiver Receiver Characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Input voltage range	V_{IN}	0		V_{DDA} + 0.3	V	
Differential peak-to-peak amplitude	V_{IDPP}	140		1250	mV	
Differential termination	V_{ITERM}		85		Ω	
	V_{ITERM}		100		Ω	
	V_{ITERM}		150		Ω	
Common mode voltage	V_{ICMDC} [1]	0.7 × V_{DDA}		0.9 × V_{DDA}	V	DC coupled
Exit electrical idle detection time	T_{EIDET}		50	100	ns	
Run length of consecutive identical digits (CID)	C_{ID}			200	UI	
CDR PPM tolerance[2]	C_{DRPPM}			1.15	% UI	
CDR lock-to-data time	T_{LTD}				CDR_{REFCLK} UI	
CDR lock-to-ref time	T_{LTF}				CDR_{REFCLK} UI	
Loss-of-signal detect (Peak Detect Range setting = high)[9]	$V_{DETLHIGH}$				mV	Setting = 1
	$V_{DETLHIGH}$				mV	Setting = 2
	$V_{DETLHIGH}$				mV	Setting = 3
	$V_{DETLHIGH}$				mV	Setting = 4
	$V_{DETLHIGH}$				mV	Setting = 5
	$V_{DETLHIGH}$				mV	Setting = 6
	$V_{DETLHIGH}$				mV	Setting = 7
Loss-of-signal detect (Peak Detect Range setting = low)[9]	V_{DETLOW}	65		175	mV	Setting = PCIe[3,7]
	V_{DETLOW}	95		190	mV	Setting = SATA[4,8]
	V_{DETLOW}	75		170	mV	Setting = 1
	V_{DETLOW}	95		185	mV	Setting = 2
	V_{DETLOW}	100		190	mV	Setting = 3
	V_{DETLOW}	140		210	mV	Setting = 4
	V_{DETLOW}	155		240	mV	Setting = 5
	V_{DETLOW}	165		245	mV	Setting = 6
	V_{DETLOW}	170		250	mV	Setting = 7
Sinusoidal jitter tolerance	T_{SJTOL}				UI	>8.5 Gbps – 12.7 Gbps [5, 10]

7.5.7 CPRI

The following table describes CPRI.

Table 66 • CPRI

	Data Rate	Min	Max	Unit
Total transmit jitter	0.6144 Gbps			UI
	1.2288 Gbps			UI
	2.4576 Gbps			UI
	3.0720 Gbps			UI
	4.9152 Gbps			UI
	6.1440 Gbps			UI
	9.8304 Gbps			UI
	10.1376 Gbps			UI
	12.16512 Gbps [1]			UI
Receive jitter tolerance	0.6144 Gbps			UI
	1.2288 Gbps			UI
	2.4576 Gbps			UI
	3.0720 Gbps			UI
	4.9152 Gbps			UI
	6.1440 Gbps			UI
	9.8304 Gbps			UI
	10.1376 Gbps			UI
	12.16512 Gbps [1]			UI

1. For data rates greater than 10.3125 Gbps, VDDA must be set to 1.05 V mode. See supply tolerance in the section Recommended Operating Conditions (see page 6).

7.5.8 JESD204B

The following table describes JESD204B.

Table 67 • JESD204B

Parameter	Data Rate	Min	Max	Unit
Total transmit jitter	3.125 Gbps		0.35	UI
	6.25 Gbps		0.3	UI
	12.5 Gbps[1]			UI
Receive jitter tolerance	3.125 Gbps	0.56		UI
	6.25 Gbps	0.6		UI
	12.5 Gbps[1]			UI

1. For data rates greater than 10.3125 Gbps, VDDA must be set to 1.05V mode. See supply tolerance in the section Recommended Operating Conditions (see page 6).

7.6 Non-Volatile Characteristics

The following section describes non-volatile characteristics.

Table 75 • FPGA Programming Cycles Lifetime Factor

Programming T_J	Programming Cycles	LF
–40 °C to 100 °C	500	1
–40 °C to 85 °C	1000	0.8
–40 °C to 55 °C	2000	0.6

Notes:

- The maximum number of device digest cycles is 100K.
- Digests are operational only over the –40 °C to 100 °C temperature range.
- After a program cycle, an additional N digests cycles are allowed with the resultant retention characteristics for the total operating and storage temperature shown.
- Retention is specified for total device storage and operating temperature.
- All temperatures are junction temperatures (T_J).
- Example 1—500 digests cycles are performed between programming cycles. N = 500. The operating conditions are –40 °C to 85 °C T_J. 501 programming cycles have occurred. The retention under these operating conditions is 20 × LF = 20 × .8 = 16 years.
- Example 2—one programming cycle has occurred, N = 1500 digest cycles have occurred. Temperature range is –40 °C to 100 °C. The resultant retention is 10 × LF or 10 years over the industrial temperature range.

7.6.5 Digest Time

The following table describes digest time.

Table 76 • Digest Times

Parameter	Devices	Typ	Max	Unit
Setup time	All	2		µs
Fabric digest run time	MPF100T, TL, TS, TLS			ms
	MPF200T, TL, TS, TLS	1005	1072	ms
	MPF300T, TL, TS, TLS	1503.9	1582	ms
	MPF500T, TL, TS, TLS			ms
UFS CC digest run time	MPF100T, TL, TS, TLS			µs
	MPF200T, TL, TS, TLS	33.2	35	µs
	MPF300T, TL, TS, TLS	33.2	35	µs
	MPF500T, TL, TS, TLS			µs
sNVM digest run time[1]	MPF100T, TL, TS, TLS			ms
	MPF200T, TL, TS, TLS	4.4	4.8	ms
	MPF300T, TL, TS, TLS	4.4	4.8	ms
	MPF500T, TL, TS, TLS			ms
UFS UL digest run time	MPF100T, TL, TS, TLS			µs
	MPF200T, TL, TS, TLS	46.6	48.8	µs
	MPF300T, TL, TS, TLS	46.6	48.8	µs
	MPF500T, TL, TS, TLS			µs
User key digest run time[2]	MPF100T, TL, TS, TLS			µs
	MPF200T, TL, TS, TLS	525.4	543.3	µs
	MPF300T, TL, TS, TLS	525.4	543.3	µs
	MPF500T, TL, TS, TLS			µs

Parameter	Devices	Typ	Max	Unit
UFS UPERM digest run time	MPF100T, TL, TS, TLS			µs
	MPF200T, TL, TS, TLS	33.2	34.9	µs
	MPF300T, TL, TS, TLS	33.2	34.9	µs
	MPF500T, TL, TS, TLS			µs
Factory digest run time	MPF100T, TL, TS, TLS			µs
	MPF200T, TL, TS, TLS	493.6	510.1	µs
	MPF300T, TL, TS, TLS	493.6	510.1	µs
	MPF500T, TL, TS, TLS			µs

1. The entire sNVM is used as ROM.
2. Valid for user key 0 through 6.

Note: These times do not include the power-up to functional timing overhead when using digest checks on power-up.

7.6.6 Zeroization Time

The following tables describe zeroization time. A zeroization operation is counted as one programming cycle.

Table 77 • Zeroization Times for MPF100T, TL, TS, and TLS Devices

Parameter	Typ	Max	Unit	Conditions
Time to enter zeroization			ms	Zip flag set
Time to destroy the fabric data[1]			ms	Data erased
Time to destroy data in non-volatile memory (like new)[1, 2]			ms	One iteration of scrubbing
Time to destroy data in non-volatile memory (recoverable)[1, 3]			ms	One iteration of scrubbing
Time to destroy data in non-volatile memory (non-recoverable)[1, 4]			ms	One iteration of scrubbing
Time to scrub the fabric data[1]			s	Full scrubbing
Time to scrub the pNVM data (like new)[1, 2]			s	Full scrubbing
Time to scrub the pNVM data (recoverable)[1, 3]			s	Full scrubbing
Time to scrub the fabric data pNVM data (non-recoverable)[1, 4]			s	Full scrubbing
Time to verify[5]			s	

1. Total completion time after entering zeroization.
2. Like new mode—zeroizes user design security setting and sNVM content.
3. Recoverable mode—zeroizes user design security setting, sNVM and factory keys.
4. Non-recoverable mode—zeroizes user design security setting, sNVM and factory keys, and factory data required for programming.
5. Time to verify after scrubbing completes.

Table 78 • Zeroization Times for MPF200T, TL, TS, and TLS Devices

Parameter	Typ	Max	Unit	Conditions
Time to enter zeroization			ms	Zip flag set
Time to destroy the fabric data[1]			ms	Data erased
Time to destroy data in non-volatile memory (like new)[1, 2]			ms	One iteration of scrubbing

Devices	IAP	FlashPro4	FlashPro5	BP	Silicon Sculptor	Units
MPF500T, TL, TS, TLS						

Notes:

- FlashPro4 4 MHz TCK.
- FlashPro5 10 MHz TCK.
- PC configuration: Intel i7 at 3.6 GHz, 32 GB RAM, Windows 10.

Table 83 • Verify System Services

Parameter	Symbol	ServiceID	Devices	Typ	Max	Unit
In application verify by index	$T_{IAP\_Ver\_Index}$	44H	MPF100T, TL, TS, TLS			s
			MPF200T, TL, TS, TLS	8.2	9	s
			MPF300T, TL, TS, TLS	12.4	13	s
			MPF500T, TL, TS, TLS			s
In application verify by SPI address	$T_{IAP\_Ver\_Addr}$	45H	MPF100T, TL, TS, TLS			s
			MPF200T, TL, TS, TLS	8.2	9	s
			MPF300T, TL, TS, TLS	12.4	13	s
			MPF500T, TL, TS, TLS			s

7.6.8 Authentication Time

The following tables describe authentication system service time.

Table 84 • Authentication Services

Parameter	Symbol	ServiceID	Devices	Typ	Max	Unit
Bitstream Authentication	T_{BIT_AUTH}	22H	MPF100T, TL, TS, TLS			s
			MPF200T, TL, TS, TLS	3.3	3.7	s
			MPF300T, TL, TS, TLS	4.9	5.4	s
			MPF500T, TL, TS, TLS			s
IAP Image Authentication	T_{IAP_AUTH}	23H	MPF100T, TL, TS, TLS			s
			MPF200T, TL, TS, TLS	3.3	3.7	s
			MPF300T, TL, TS, TLS	4.9	5.4	s
			MPF500T, TL, TS, TLS			

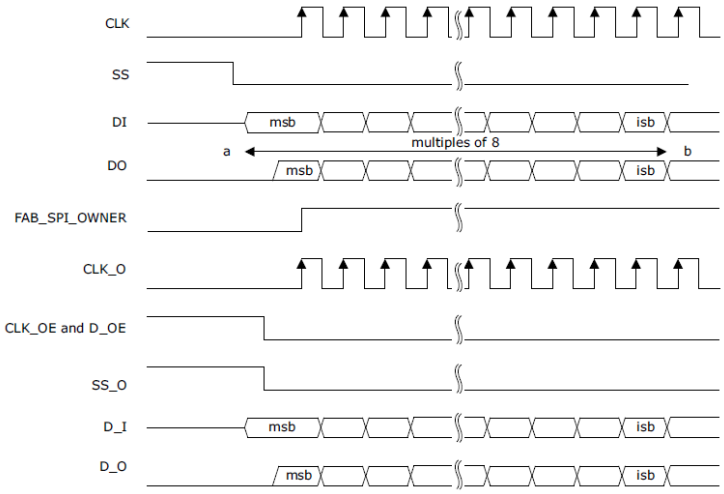
7.6.9 Secure NVM Performance

The following table describes secure NVM performance.

Table 85 • sNVM Read/Write Characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Conditions
Plain text programming		7.0	7.2	7.9	ms	
Authenticated text programming		7.2	7.4	9.4	ms	
Authenticated and encrypted text programming		7.2	7.4	9.4	ms	
Authentication R/W 1st access from power-up overhead	T_{PUF_OVHD}		100	111	ms	From T_{FAB_READY}
Plain text read		7.67	7.79	8.2	µs	

Figure 4 • USPI Switching Characteristics



7.8.4 Tamper Detectors

The following section describes tamper detectors.

Table 91 • ADC Conversion Rate

Parameter	Description	Min	Typ[1]	Max
T_{CONV1}	Time from enable changing from zero to non-zero value to first conversion completes. Minimum value applies when POWEROFF = 0.	420 µs		470 µs
T_{CONVN}	Time between subsequent channel conversions.		480 µs	
T_{SETUP}	Data channel and output to valid asserted. Data is held until next conversion completes, that is >480 µs.	0 ns		
T_{VALID}[2]	Width of the valid pulse.	1.625 µs		2 µs
T_{RATE}	Time from start of first set of conversions to the start of the next set. Can be considered as the conversion rate. Is set by the conversion rate parameter.	480 µs	Rate × 32 µs	8128 µs

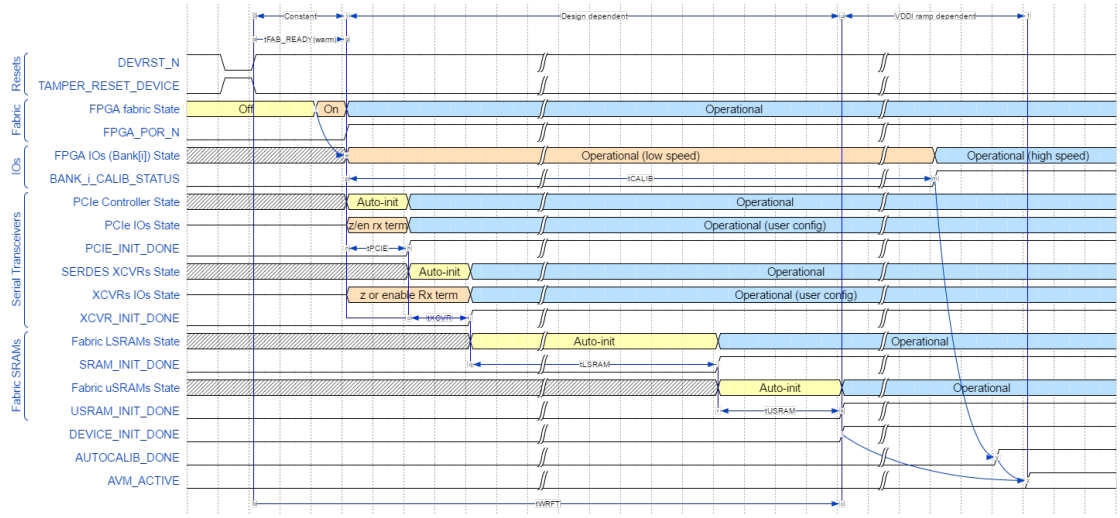
1. Min, typ, and max refer to variation due to functional configuration and the raw TVS value. The actual internal correction time will vary based on the raw TVS value.
2. The pulse width varies depending on the time taken to complete the internal calibration multiplication, this can be up to 375 ns.

Note: Once the TVS block is active, the enable signal is sampled 25 ns before the falling edge of valid. The next enabled channel in the sequence 0-1-2-3 is started; that is, if channel 0 has just completed and only channels 0 and 3 are enabled, the next channel will be 3. When all the enabled channels in the sequence 0-1-2-3 are completed, the TVS waits for the conversion rate timer to expire. The enable signal may be changed at any time if it changes to 4'b0000 while valid is asserted (and 25 ns before valid is de-asserted), then no further conversions will be started.

Table 92 • Temperature and Voltage Sensor Electrical Characteristics

Parameter	Min	Typ	Max	Unit	Condition
Temperature sensing range	–40		125	°C	
Temperature sensing accuracy	–10		10	°C	

Figure 6 • Warm Reset Timing



7.9.3 Power-On Reset Voltages

7.9.3.1 Main Supplies

The start of power-up to functional time (T_{PUFT}) is defined as the point at which the latest of the main supplies (VDD, VDD18, VDD25) reach the reference voltage levels specified in the following table. This starts the process of releasing the reset of the device and powering on the FPGA fabric and IOs.

Table 97 • POR Ref Voltages

Supply	Power-On Reset Start Point (V)	Note
VDD	0.95	Applies to both 1.0 V and 1.05 V operation.
VDD18	1.71	
VDD25	2.25	

7.9.3.2 I/O-Related Supplies

For the I/Os to become functional (for low speed, sub 400 MHz operation), the (per-bank) I/O supplies (VDDI, VDDAUX) must reach the trip point voltage levels specified in the following table and the main supplies above must also be powered on.

Table 98 • I/O-Related Supplies

Supply	I/O Power-Up Start Point (V)
VDDI	0.85
VDDAUX	1.6

There are no sequencing requirements for the power supplies. However, VDDI3 and must be valid at same time as the main supplies. The other IO supplies (VDDI, VDDAUX) have no effect on power-up of FPGA fabric (that is, the fabric still powers up even if the IO supplies of some IO banks remain powered off).